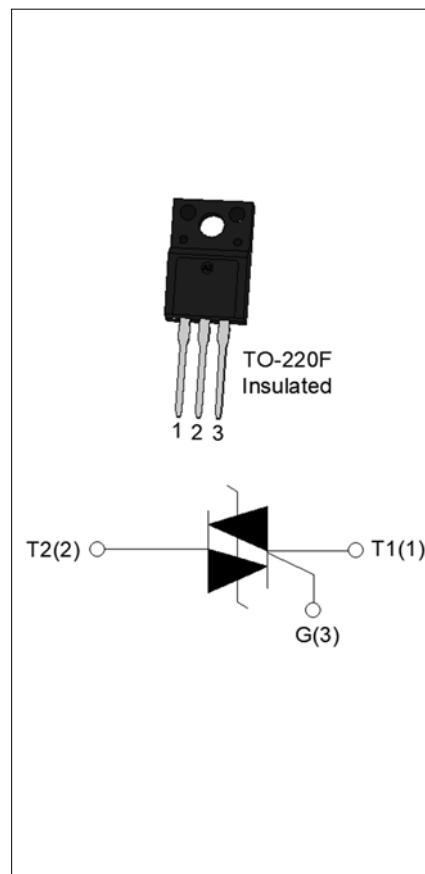


**DESCRIPTION:**

The ACJT1210-10F triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The ACJT1210-10F embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. By using an external plastic package, ACJT1210-10F provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	1000	V
$I_{GT\text{ I/II/III}}$	10/10/10	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	1000	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	1000	V
RMS on-state current ($T_c \leqslant 86^\circ\text{C}$)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	120	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		132	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	72	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	dI/dt	50	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	4	A

Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	4.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	I - II - III	MAX.	10	mA
V_{GT}		I - II - III	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3\text{k}\Omega$	I - II - III	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I - III	MAX.	25	mA
		II		30	
I_H	$I_T=500\text{mA}$		MAX.	20	mA
dV/dt	$V_D=670\text{V}$ Gate Open $T_j=125^\circ\text{C}$		MIN.	300	V/ μs
$(dI/dt)c$	$(dV/dt)c=10\text{V}/\mu\text{s}$, $T_j=125^\circ\text{C}$		MIN.	3	A/ms
t_{on}	$I_G=20\text{mA}$ $I_A=200\text{mA}$ $I_R=20\text{mA}$ $T_j=25^\circ\text{C}$	TYP.	4	μs	
t_{off}			50		
V_{CL}	$I_{CL}=0.1\text{mA}$ $t_p=1\text{ms}$		MIN.	1050	V

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit	
V_{TM}	$I_{TM}=17\text{A}$	$t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.45	V
V_{TO}	Threshold voltage		$T_j=125^\circ\text{C}$	0.8	V
R_D	Dynamic resistance		$T_j=125^\circ\text{C}$	34	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM}$	$V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	10	μA
I_{RRM}			$T_j=125^\circ\text{C}$	1	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2.4	$^\circ\text{C/W}$
$R_{th(j-a)}$	junction to ambient (AC)	60	$^\circ\text{C/W}$

ORDERING INFORMATION

<u>AC</u>	<u>J</u>	<u>T</u>	<u>12</u>	<u>10</u>	<u>-10</u>	<u>F</u>
<u>AC switch</u>						
<u>JieJie Microelectronics Co.,Ltd.</u>		<u>Triacs</u>				
			<u> IT(RMS):12A</u>			
				<u>10: IGT1-3≤10mA</u>		
						<u>F:TO-220F(Ins)</u>
						<u>10: VDRM /VRRM≥1000V</u>

MARKING

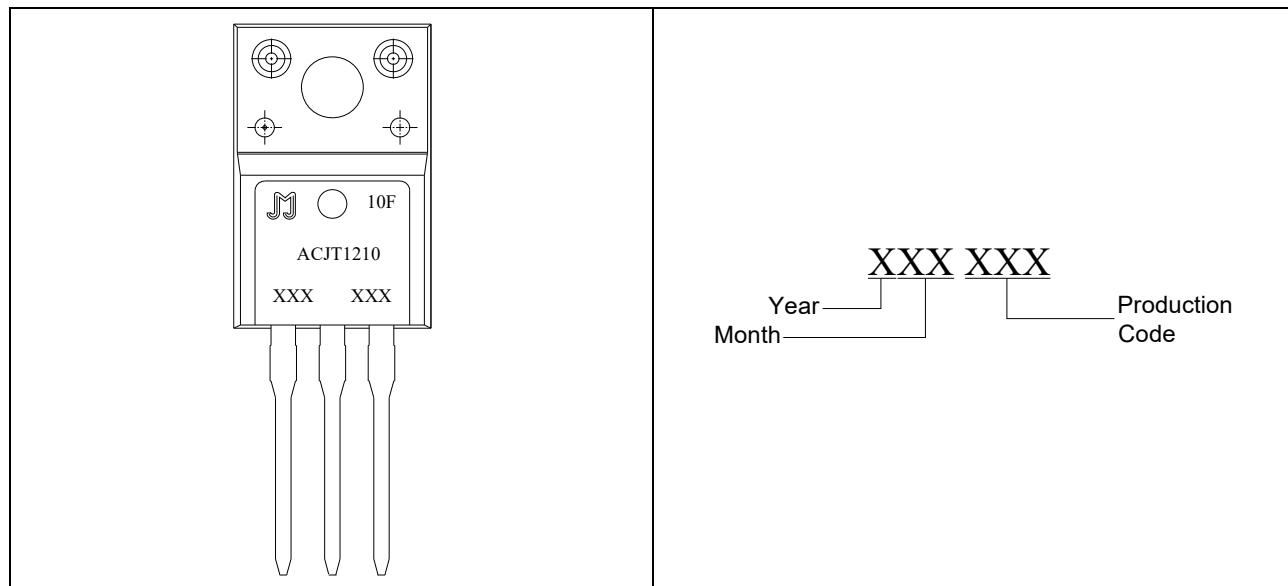


FIG.1 Maximum power dissipation versus RMS on-state current

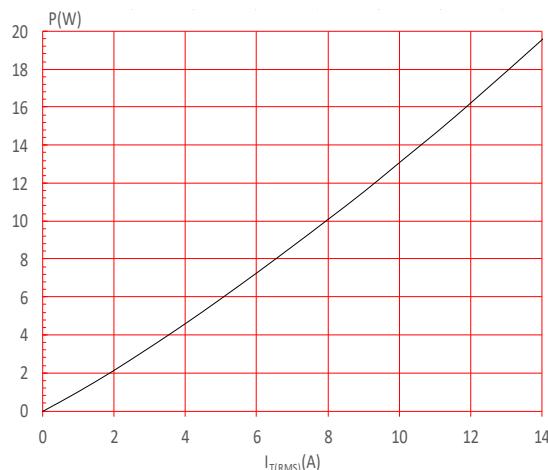


FIG.3: Surge peak on-state current versus number of cycles

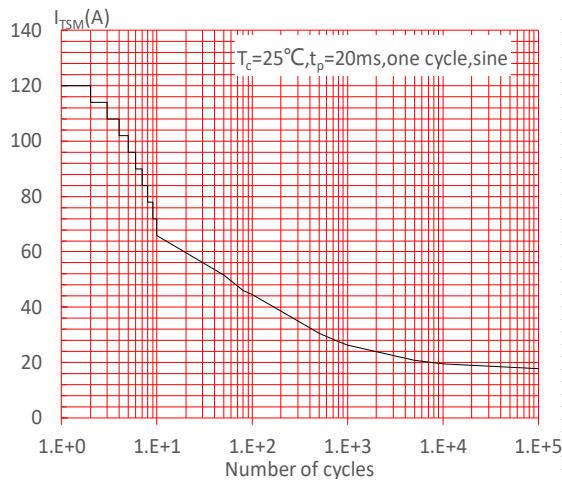


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($dI/dt < 50\text{A}/\mu\text{s}$)

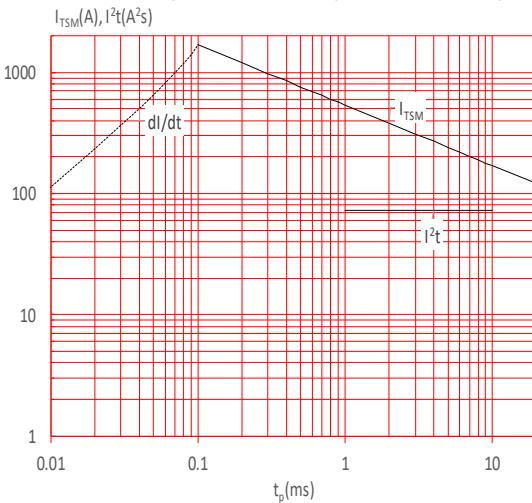


FIG.2: RMS on-state current versus case temperature

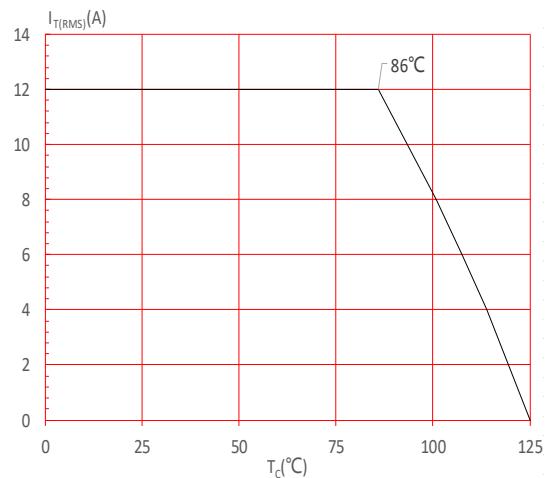


FIG.4: On-state characteristics

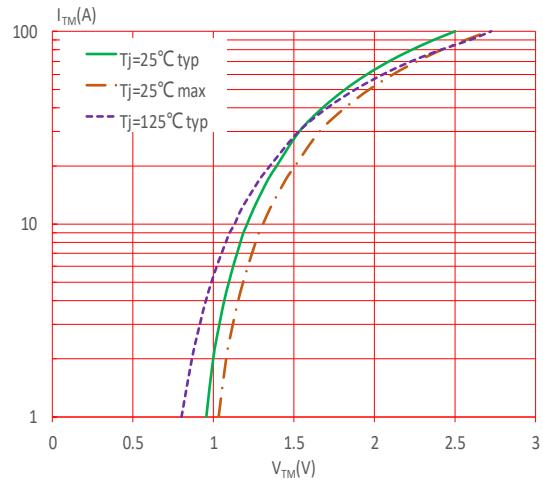


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

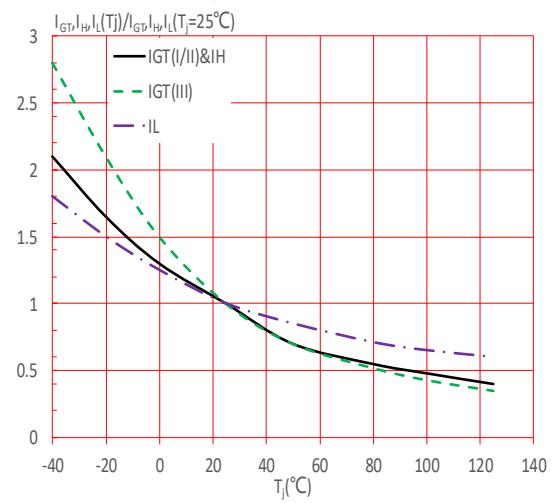
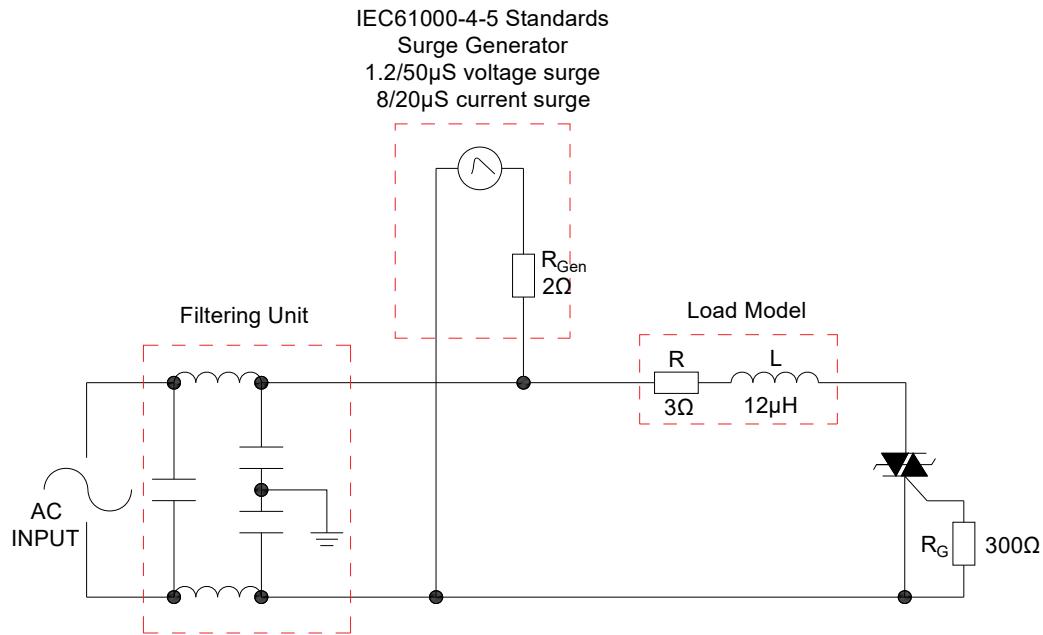


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SHAPING AND SOLDERING PARAMETERS

Refer to «Instructions for installation of plastic-sealed in-line power devices» released by JieJie

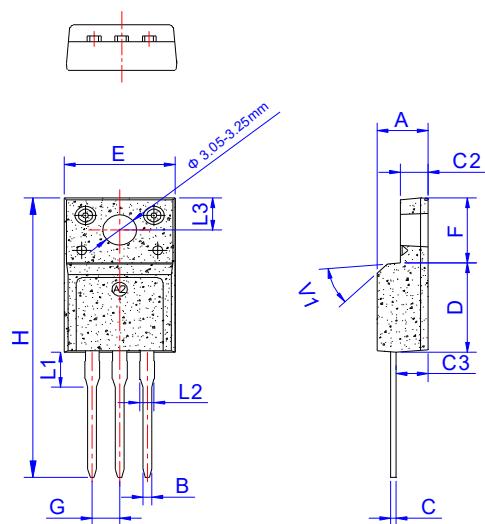
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
ACJT1210-10F	1000	10	TO-220F(Ins)	50	Tube

Document Revision History

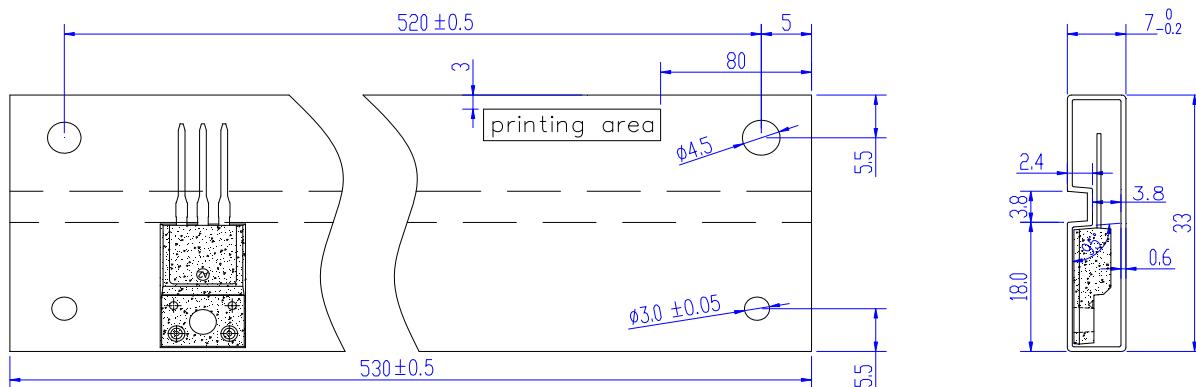
Date	Revision	Changes
Apr.13, 2023	A.1.0	Last updated

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	3.20		3.80	0.126		0.150
L2	1.14		1.70	0.045		0.067
L3	3.20		3.60	0.126		0.142
V1		45°			45°	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220F	TUBE	50	1,000	5,000

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